

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

HACENE LAHRECHE, ET AL.

For: **method for epitaxial growth of a gallium
nitride film separated from its substrate**

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

PRELIMINARY AMENDMENT

Dear Sir:

Please enter the following preliminary amendment for the present patent application.

In the Specification:

After the title, please insert the following:

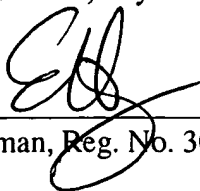
--The present patent application is a non-provisional application of International Application No.
PCT/FR2003/001615, filed May 28, 2003.--

Respectfully submitted,

Blakely, Sokoloff, Taylor & Zafman LLP

Dated:

11/27/03


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